



ZXT13N50DE6

50V NPN LOW SATURATION SWITCHING TRANSISTOR

Features

- BV_{CEO} > 50V
- I_C = 4A Continuous Collector Current
- I_{CM} = 10A Peak Pulse Current
- R_{CE(SAT)} = 36mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage (100mV max @ 1A)
- h_{FE} Characterized up to 10A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.015 grams (Approximate)

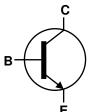
Applications

- DC-DC Converters
- Power Management Functions
- Power Switches
- Motor Control

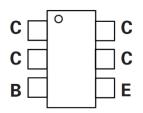
SOT26



Top View



Device Symbol



Top View Pin-Out

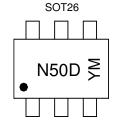
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXT13N50DE6TA	AEC-Q101	N50D	7	8	3,000
ZXT13N50DE6TC	AEC-Q101	N50D	13	8	10,000
ZXT13N50DE6QTA	Automotive	N50D	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N50D = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015)

M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	;	2016	2017	2018	2019	2020	202	20	22 :	2023	2024	2025
Code	O		D	Е	F	G	Н	-	,	J	K	L	М
Monti	h	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code)	1	2	3	4	5	6	7	8	9	0	N	D

ZXT13N50DE6
Document Number: DS33636 Rev. 4 - 2



Absolute Maximum Ratings (@T_A = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7.5	V
Base Current	I _B	500	mA
Continuous Collector Current	Ic	4	Α
Peak Pulse Collector Current	I _{CM}	10	Α

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	Б	1.1 8.8	W mW/°C	
Linear Derating Factor	(Note 7)	- P _D	1.7 13.6		
Thermal Decistance, Junction to Ambient	(Note 6)	Б	113		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	73	°C/W	
Thermal Resistance, Junction to Lead (Note		$R_{\theta JL}$	18.6		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

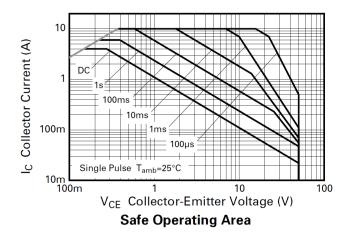
Notes:

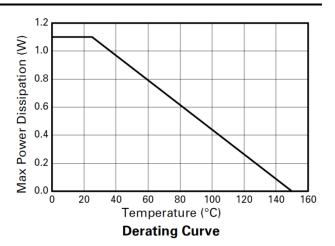
- 6. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is measured at $t \le 5$ sec.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead). 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

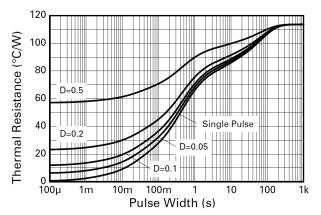




Thermal Characteristics and Derating Information







Transient Thermal Impedance



Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_CBO	100	190	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	50	70	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7.5	8.5	_	V	$I_E = 100\mu A$
Collector-Base Cutoff Current	I _{CBO}		_	100	nA	V _{CB} = 80V
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 6V
Collector-Emitter Cutoff Current	I _{CES}	_	_	100	nA	V _{CES} = 80V
ON CHARACTERISTICS (Note 10)						
		250	400	_		$I_C = 10$ mA, $V_{CE} = 2$ V
DC Current Gain	h	300	450	900		I _C = 1A, V _{CE} = 2V
DO Guilent Gain	h _{FE}	100	220	_		$I_C = 4A$, $V_{CE} = 2V$
		10	30	_		I _C = 10A, V _{CE} = 2V
			8	12		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$
			75	100		$I_C = 1A, I_B = 10mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		150	200	mV	$I_C = 3A$, $I_B = 50mA$
			175	230		$I_C = 4A, I_B = 100mA$
			145	180		$I_C = 4A, I_B = 400mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		_	1.0	V	$I_C = 4A, I_B = 100mA$
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	_	0.9	V	I _C = 4A, V _{CE} = 2V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T		115	_	MHz	$V_{CE} = 10V, I_{C} = 50mA, f = 50MHz$
Output Capacitance	C _{obo}		31	_	pF	V _{CB} = 10V, f = 1MHz
Turn-On Time	t _(on)	1	220	_	ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	t _(off)		830	_	ns	$I_{B1} = I_{B2} = 20mA$

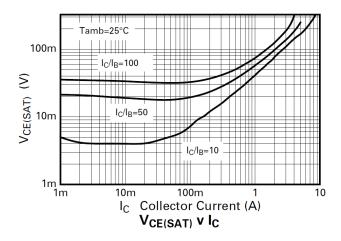
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

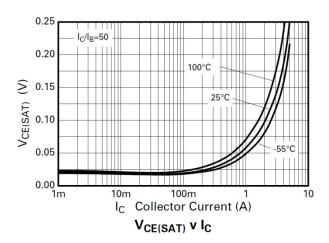
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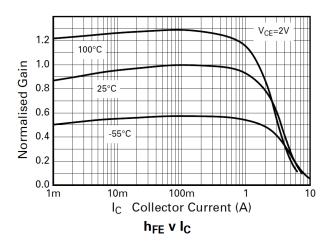


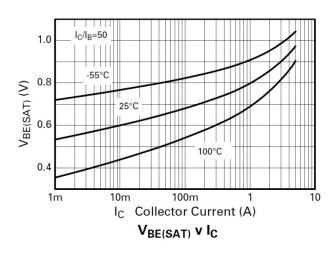


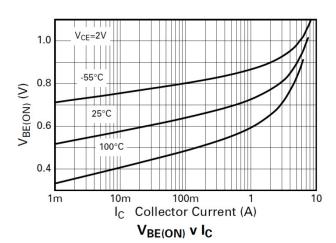
Typical Electrical Characteristics (@T_A = +25 ℃, unless otherwise specified.)







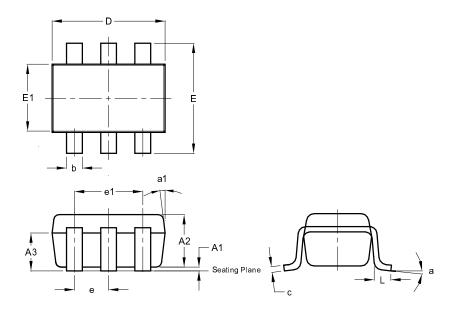






Package Outline Dimensions

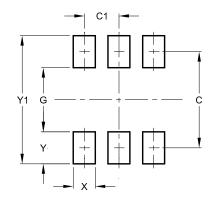
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26						
Dim	Min	Max	Тур			
A1	0.013	0.10	0.05			
A2	1.00	1.30	1.10			
А3	0.70	0.80	0.75			
b	0.35	0.50	0.38			
С	0.10	0.20	0.15			
D	2.90	3.10	3.00			
е	-	-	0.95			
e1	1	1	1.90			
Е	2.70	3.00	2.80			
E1	1.50	1.70	1.60			
L	0.35	0.55	0.40			
а	-	-	8°			
a1	-	-	7°			
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
X	0.55
Υ	0.80
Y1	3.20





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